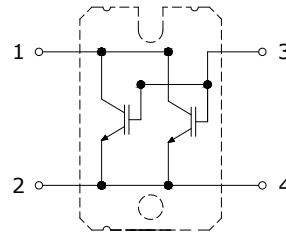


PRELIMINARY DATASHEET
IGBT in Trench & Field Stop-technology in Isolated SOT227 Package

- Very high switching speed
- Very low VCE(sat)
- Short circuit withstand time – 5 μ s
- Designed for frequency converters and UPS
- Very tight parameter distribution
- High ruggedness, temperature stability
- Parallel switching capability
- Pb-free lead finish; RoHS compliant


MAXIMUM RATINGS (per IGBT)), at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Units
Collector-emitter voltage	V_{CE}	600	V
DC collector current, limited by T_{jmax} $T_C = 25^\circ\text{C}$ $T_C = 80^\circ\text{C}$	I_C	300 150	A
Pulsed collector current, t_D limited by T_{jmax}	I_{Cpulse}	450	
Turn off safe operating area $V_{CE} \leq 1200\text{V}$, $T_j \leq 150^\circ\text{C}$	-	450	
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time ¹ $V_{GE} = 15\text{V}$, $V_{CC} \leq 400\text{V}$, $T_j \leq 150^\circ\text{C}$	t_{sc}	5	μs
Soldering temperature Wave soldering, 1.6 mm (0.063 in.) from case for 10s	T_S	260	$^\circ\text{C}$
Operating junction and storage temperature	T_j, T_{stg}	-55... +175	$^\circ\text{C}$

Thermal and Isolation Characteristics (per IGBT)

Parameter	Symbol	Max. Value	Units
Characteristics			
IGBT thermal resistance, junction to case	R_{thJC}	0.46	K/W
Thermal resistance, junction to ambient	R_{thJA}	40	
Isolation voltage, RMS (measured between terminals and mounting base, 50-60 Hz, for 1-3 seconds)	V_{iso}	3000	V

¹ Allowed number of short circuits: < 1000; time between short circuits: > 1s.

CAUTION: These devices are ESD sensitive. Use proper handling procedure.

ELECTRICAL CHARACTERISTICS (per IGBT), at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{V}, I_C = 0.4\text{mA}$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{V}, I_C = 150\text{A}$ $T_j = 25^\circ\text{C}$ $T_j = 175^\circ\text{C}$	- -	1.5 1.9	2.0 -	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 2.4\text{mA}, V_{CE} = V_{GE}$	4.1	4.9	5.7	
Zero gate voltage collector current	I_{CES}	$V_{CE} = 600\text{V}, V_{GE} = 0$ $T_j = 25^\circ\text{C}$	-	-	80	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}$	-	-	200	nA
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{CE} = 25\text{V},$ $V_{GE} = 0\text{V},$ $f = 1\text{MHz}$	-	9240	-	pF
Output capacitance	C_{oss}		-	576	-	
Reverse transfer capacitance	C_{rss}		-	274	-	
Gate charge	Q_{Gate}	$V_{CC} = 480\text{V}, I_C = 75\text{A}$ $V_{GE} = 15\text{V}$	-	940	-	nC
Short circuit collector current ¹	$I_{C(SC)}$	$V_{GE} = 15\text{V}, t_{SC} \leq 5\mu\text{s}$ $V_{CC} = 400\text{V},$ $T_j \leq 150^\circ\text{C}$	-	1375	-	A

SWITCHING CHARACTERISTICS (per IGBT), Inductive Load at $T_j = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
IGBT Characteristics						
Turn-on delay time	$t_{d(on)}$	$T_j = 25^\circ\text{C},$ $V_{CC} = 400\text{V}, I_C = 75\text{A},$ $V_{GE} = 0/15\text{V},$ $R_G = 5\Omega,$ $L_G^2 = 100\text{nH},$ $C_G^2 = 39\text{pF}$	-	33	-	ns
Rise time	t_r		-	36	-	
Turn-off delay time	$t_{d(off)}$		-	330	-	
Fall time	t_f		-	35	-	
Turn-on energy	E_{on}	Energy losses include tail and diode reverse recovery.	-	2.0	-	mJ
Turn-off energy	E_{off}		-	2.5	-	
Total switching energy	E_{ts}		-	4.5	-	

SWITCHING CHARACTERISTICS (per IGBT) , Inductive Load at $T_j = 150^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
IGBT Characteristics						
Turn-on delay time	$t_{d(on)}$	$T_j = 150^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=75\text{A}$, $V_{GE}=0\text{V}/15\text{V}$, $R_G=5\Omega$, $L_\sigma^2 = 100\text{nH}$, $C_\sigma^2 = 39\text{pF}$	-	32	-	ns
Rise time	t_r		-	37	-	
Turn-off delay time	$t_{d(off)}$		-	363	-	
Fall time	t_f		-	38	-	
Turn-on energy	E_{on}	Energy losses include tail and diode reverse recovery.	-	2.9	-	mJ
Turn-off energy	E_{off}		-	2.9	-	
Total switching energy	E_{ts}		-	5.8	-	

1 Allowed number of short circuits: < 1000; time between short circuits: > 1s.
 2 Leakage inductance L_σ and Stray capacity C_σ due to dynamic test circuit.

Package Outline Drawing
